

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
 - a light-transmitting substrate;
 - a base film having a projection, the film being formed over one surface of the light-transmitting substrate;
 - an island-like semiconductor layer having a crystal structure entirely covering the projection and extending over a pair of edges of the projection;
 - a gate insulating film over the island-like semiconductor layer; and
 - a gate electrode over the gate insulating film.

2. (Currently Amended) A semiconductor device comprising:
 - a light-transmitting substrate;
 - a base film having a projection is provided over one surface of the light-transmitting substrate;
 - a thin film transistor comprising:
 - an island-like semiconductor layer comprising a channel formation region, wherein at least a part of the channel formation region is provided over the projection, and wherein the island-like semiconductor layer entirely covers the projection and extends over a pair of edges of the projection;
 - a gate insulating film over the island-like semiconductor layer; and
 - a gate electrode over the gate insulating film.

3. (Previously Presented) A semiconductor device according to claim 1, wherein a height of the projection is 30 to 100 nm.

4. (Previously Presented) A semiconductor device according to claim 2, wherein a height of the projection is 30 to 100 nm.

5.-10. (Canceled)

11. (Currently Amended) A semiconductor device comprising:

a light-transmitting substrate;

a base film having a region of a first thickness and a region of a second thickness, over one surface of the light-transmitting substrate, wherein the second thickness is smaller than the first thickness, and wherein an area of the region of the first thickness is smaller than an area of the region of the second thickness;

an island-like semiconductor layer having a crystal structure over the region of the first thickness and the region of the second thickness,

a gate insulating film over the island-like semiconductor layer; and

a gate electrode over the gate insulating film,

~~wherein the island-like semiconductor layer is capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness.~~

wherein the island-like semiconductor layer entirely covers the region of the first thickness.

12. (Currently Amended) A semiconductor device comprising:

a light-transmitting substrate;

a base film having a region of a first thickness and a region of a second thickness, over one surface of the light-transmitting substrate, wherein the second thickness is smaller than the first thickness, and wherein an area of the region of the first thickness is smaller than an area of the region of the second thickness;

a thin film transistor comprising:

a channel formation region, wherein at least a part of the channel formation region is provided over the region of the first thickness;

source and drain ~~regions over~~ regions, wherein at least a part of the source and drain regions is provided over the region of the second thickness,

~~wherein the channel formation region, and the source and drain regions are capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness;~~

wherein the channel formation region and the source and drain regions entirely cover the region of the first thickness;

a gate insulating film over the channel formation region, and the source and drain regions; and

a gate electrode over the gate insulating film.

13. (Previously Presented) A semiconductor device according to claim 11, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

14. (Previously Presented) A semiconductor device according to claim 12, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

15. (Previously Presented) A semiconductor device according to claim 1, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

16. (Previously Presented) A semiconductor device according to claim 2, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

17. (Previously Presented) A semiconductor device according to claim 11, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

18. (Previously Presented) A semiconductor device according to claim 12, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

19. (Previously Presented) A semiconductor device according to claim 1, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

20. (Previously Presented) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

21. (Previously Presented) A semiconductor device according to claim 11, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an

electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

22. (Previously Presented) A semiconductor device according to claim 12, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.